ADE-208-042C(Z)

HVM121WK
Silicon Epitaxial Planar PIN Diode for High Frequency Attenuator

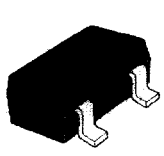
HITACHI

Preliminary
Rev. 3
Jun. 1993

Features

- Low capacitance. (C= 0.7pF max)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Pin Arrangement



(Top View)

1 Anode
2 Anode
3 Cathode

Ordering Information

Type No.	Laser Mark	Package Code
HVM121WK	H 4	MPAK

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	100	V
Forward current	I_F	50	mA
Power dissipation	P_d *	100	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

* Per one device

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.1	V	I_F = 50 mA
Reverse current	I_R	—	—	100	nA	V_R = 30 V
Capacitance	C	—	—	0.7	pF	V_R = 50 V, f = 1 MHz
Forward resistance	r_{f1}	1.0	—	—	kΩ	I_F = 10 μA, f = 100 MHz
	r_{f2}	—	—	10	Ω	I_F = 10 mA, f = 100 MHz

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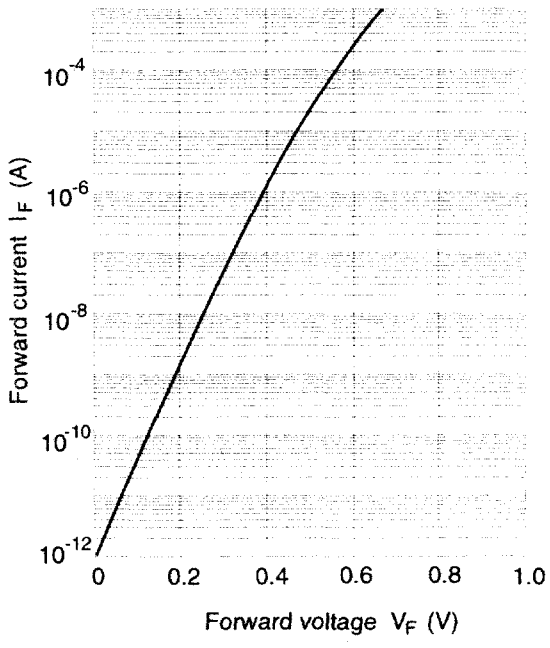


Fig.1 Forward current Vs. Forward voltage

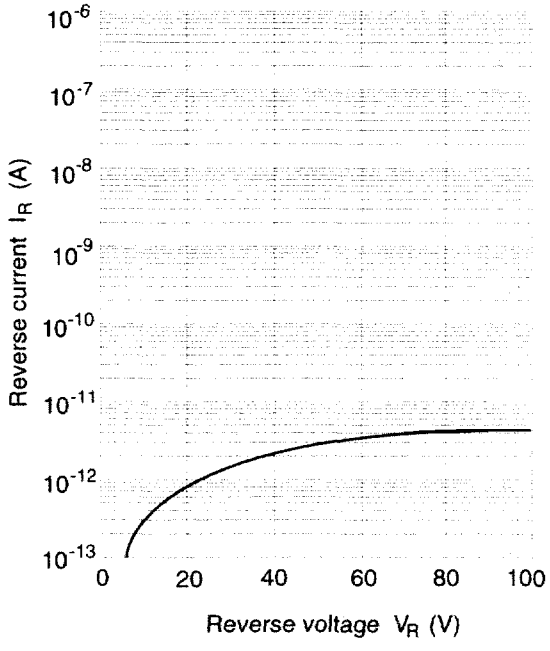


Fig.2 Reverse current Vs. Reverse voltage

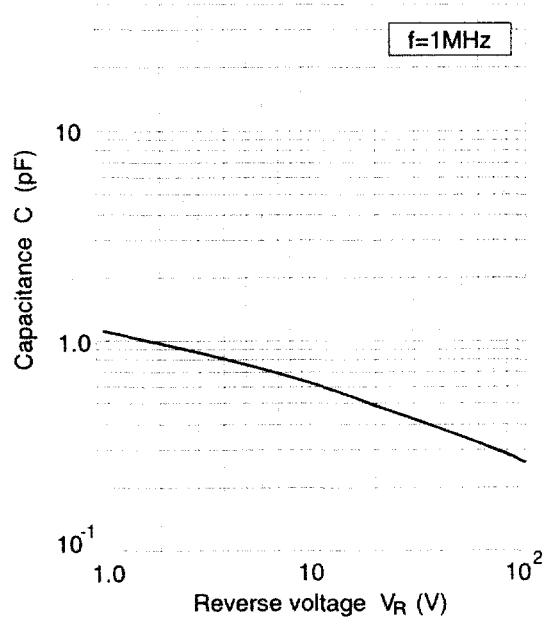


Fig.3 Capacitance Vs. Reverse voltage

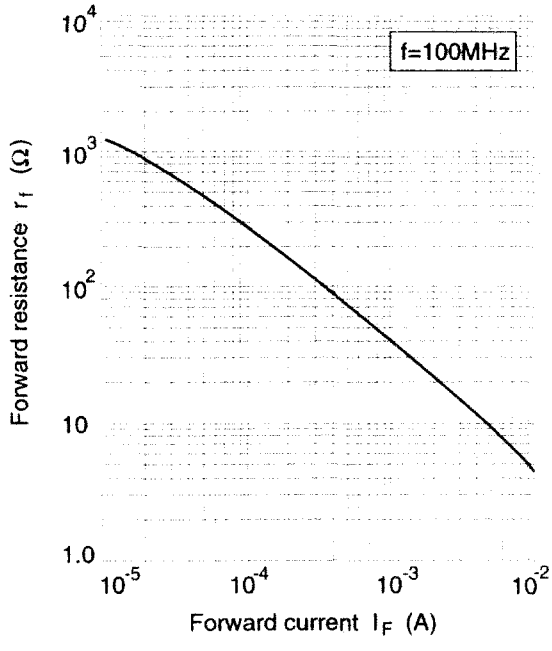
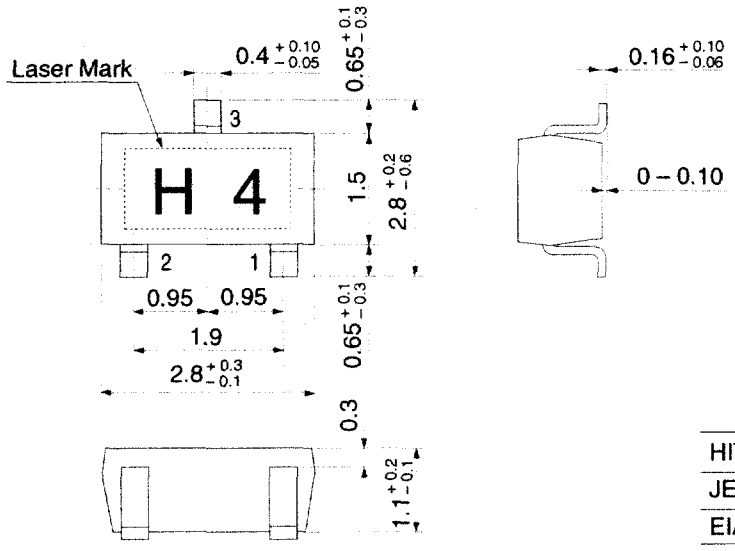


Fig.4 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm



1 Anode
2 Anode
3 Cathode

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011